GLASS LOW-K DIELECTRIC ETCH APPLICATIONS, by Rao V. Annapragada et al., filed concurrently herewith and incorporated herein by reference.

This application is also related to the commonly assigned U.S. Patent Application No.: [_____ (Attorney Docket No. LAM1P153/P0693)] 09/782,437 entitled USE OF HYDROCARBON ADDITION FOR THE ELIMINATION OF MICROMASKING DURING ETCHING OF ORGANIC LOW-K DIELECTRICS, by Chok W. Ho, filed concurrently herewith and incorporated herein by reference."

In the Claims:

Please cancel claims 1-3, 12 and 17-19.

Please amend claims 4, and 13 and add claims 20-24, as follows:

1. (Cancelled)

2. (Cancelled)

3. (Cancelled)

4. (Once Amended) [The] A method [, as recited in claim 3, further] of etching an organic dielectric layer over a substrate, comprising.

placing a hard mask over the organic dielectric layer;

placing a patterned photoresist layer over the hard mask layer;

placing the substrate in an etching chamber;

providing an etchant gas comprising NH3 into the etching chamber, wherein the NH3 has a flow rate between 5 sccm to 1500 sccm;

generating a plasma from the NH3, which etches the organic dielectric layer; and

simultaneously stripping the photo resist layer during the etching of the organic dielectric layer.

12. (Cancelled)

13. (Once Amended) [The] A method [, as recited in claim 12, further] of etching an organic dielectric layer over a substrate, comprising:

placing a hard mask over the organic dielectric layer;

placing a patterned photoresist layer over the hard mask layer;

placing the substrate in an etching chamber;

providing an etchant gas comprising NH3 into the etching chamber;

generating a plasma from the NH3, which etches the organic dielectric layer; and

simultaneously stripping the photo resist layer during the etching of the organic dielectric layer.

17. (Cancelled)

18. (Cancelled)

19. (Cancelled)